

95
semiconductor layer to prevent a second gallium nitride based semiconductor layer, of a material different from the first gallium nitride based semiconductor layer, from nucleating thereon. The bottom surface of the trench is of a material such that the second gallium nitride based semiconductor layer will not nucleate thereon. The second gallium nitride based semiconductor material is grown, extending from at least one of the side walls of the trench, the second gallium nitride based semiconductor material having fewer defects than the first gallium nitride based semiconductor layer.

The amendments to the claims and specification are primarily supported by pages 4-6 of the specification describing Figures 3-5.

If the examiner's next action is other than the allowance of the pending claims, the Examiner is respectfully requested to call Applicants' attorney at 408-453-9200.

I hereby certify that this correspondence is being deposited with the United States Postal Service as First Class Mail in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231, on October 26, 2001.

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10/26/01
Date of Signature

Respectfully submitted,

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